

FDMC6675BZ

P-Channel POWERTRENCH[®] MOSFET

–30 V, –20 A, 14.4 mΩ

Description

The FDMC6675BZ has been designed to minimize losses in load switch applications. Advancements in both silicon and package technologies have been combined to offer the lowest $R_{DS(on)}$ and ESD protection.

Features

- Max $R_{DS(on)}$ = 14.4 mΩ at $V_{GS} = -10$ V, $I_D = -9.5$ A
- Max $R_{DS(on)}$ = 27.0 mΩ at $V_{GS} = -4.5$ V, $I_D = -6.9$ A
- HBM ESD Protection Level of 8 kV Typical (Note 3)
- Extended V_{GSS} Range (–25 V) for Battery Applications
- High Performance Trench Technology for Extremely Low $R_{DS(on)}$
- High Power and Current Handling Capability
- These Devices are Pb-Free, Halogen Free/BFR Free and are RoHS Compliant

Typical Applications

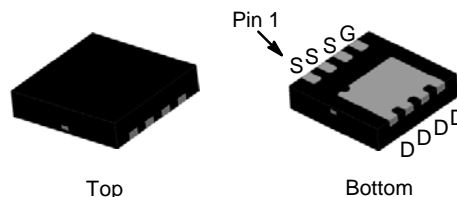
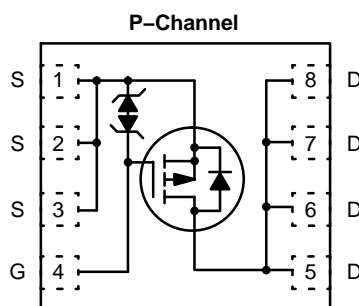
- Load Switch in Notebook and Server
- Notebook Battery Pack Power Management



ON Semiconductor[®]

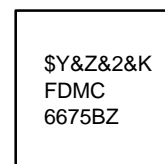
www.onsemi.com

| V_{DS} | $R_{DS(on)}$ MAX | I_D MAX |
|----------|------------------|-----------|
| –30 V | 14.4 mΩ @ 10 V | –20 A |



WDFN8 3.3x3.3, 0.65P
CASE 511DR

MARKING DIAGRAM



| | |
|------------|-------------------------|
| \$Y | = ON Semiconductor Logo |
| &Z | = Assembly Plant Code |
| &2 | = Numeric Date Code |
| &K | = Lot Code |
| FDMC6675BZ | = Specific Device Code |

ORDERING INFORMATION

See detailed ordering and shipping information on page 2 of this data sheet.

FDMC6675BZ

MOSFET MAXIMUM RATINGS (T_A = 25°C, Unless otherwise specified)

| Symbol | Parameter | Ratings | Unit |
|-----------------------------------|---|-------------|------|
| V _{DS} | Drain to Source Voltage | –30 | V |
| V _{GS} | Gate to Source Voltage | ±25 | V |
| I _D | Drain Current – Continuous T _C = 25°C | –20 | A |
| | – Continuous T _A = 25°C (Note 1a) | –9.5 | |
| | – Pulsed | –32 | |
| P _D | Power Dissipation T _C = 25°C | 36 | W |
| | Power Dissipation T _A = 25°C (Note 1a) | 2.3 | |
| T _J , T _{STG} | Operating and Storage Junction Temperature Range | –55 to +150 | °C |

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

THERMAL CHARACTERISTICS

| Symbol | Parameter | Ratings | Unit |
|------------------|---|---------|------|
| R _{θJC} | Thermal Resistance, Junction to Case | 3.4 | °C/W |
| R _{θJA} | Thermal Resistance, Junction to Ambient (Note 1a) | 53 | |

PACKAGE MARKING AND ORDERING INFORMATION

| Device Marking | Device | Package | Reel Size | Tape Width | Shipping (Qty / Packing) [†] |
|----------------|------------|--|-----------|------------|---------------------------------------|
| FDMC6675BZ | FDMC6675BZ | WDFN8 3.3x3.3, 0.65P (MLP) (Pb–Free/Halogen Free) | 13" | 12 mm | 3000 / Tape & Reel |

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

ELECTRICAL CHARACTERISTICS (T_J = 25°C unless otherwise noted)

| Symbol | Parameter | Test Conditions | Min | Typ | Max | Unit |
|--------|-----------|-----------------|-----|-----|-----|------|
|--------|-----------|-----------------|-----|-----|-----|------|

OFF CHARACTERISTICS

| | | | | | | |
|--------------------------------------|---|--|-----|-----|------------|-------|
| BV _{DSS} | Drain to Source Breakdown Voltage | I _D = –250 μA, V _{GS} = 0 V | –30 | – | – | V |
| $\frac{\Delta BV_{DSS}}{\Delta T_J}$ | Breakdown Voltage Temperature Coefficient | I _D = –250 μA, referenced to 25°C | – | –20 | – | mV/°C |
| I _{DSS} | Zero Gate Voltage Drain Current | V _{DS} = –24 V, V _{GS} = 0 V V _{DS} = –24 V, V _{GS} = 0 V, T _J = 125°C | – | – | –1 –100 | μA |
| I _{GSS} | Gate to Source Leakage Current | V _{GS} = ±25 V, V _{DS} = 0 V | – | – | ±10 | μA |

ON CHARACTERISTICS

| | | | | | | |
|--|--|--|------|------|------|-------|
| V _{GS(th)} | Gate to Source Threshold Voltage | V _{GS} = V _{DS} , I _D = –250 μA | –1.0 | –1.9 | –3.0 | V |
| $\frac{\Delta V_{GS(th)}}{\Delta T_J}$ | Gate to Source Threshold Voltage Temperature Coefficient | I _D = –250 μA, referenced to 25°C | – | –6.0 | – | mV/°C |
| R _{DS(on)} | Static Drain to Source On Resistance | V _{GS} = –10 V, I _D = –9.5 A | – | 10.7 | 14.4 | mΩ |
| | | V _{GS} = –4.5 V, I _D = –6.9 A | – | 17.4 | 27.0 | |
| | | V _{GS} = –10 V, I _D = –9.5 A, T _J = 125°C | – | 15.2 | 20.5 | |
| g _{FS} | Forward Transconductance | V _{DD} = –5 V, I _D = –9.5 A | – | 28 | – | S |

FDMC6675BZ

ELECTRICAL CHARACTERISTICS ($T_J = 25^\circ\text{C}$ unless otherwise noted)

DYNAMIC CHARACTERISTICS

| | | | | | | |
|-----------|------------------------------|--|---|------|------|----|
| C_{iss} | Input Capacitance | $V_{DS} = -15\text{ V}, V_{GS} = 0\text{ V}, f = 1\text{ MHz}$ | – | 2154 | 2865 | pF |
| C_{oss} | Output Capacitance | | – | 392 | 525 | pF |
| C_{rss} | Reverse Transfer Capacitance | | – | 349 | 525 | pF |

SWITCHING CHARACTERISTICS

| | | | | | | |
|--------------|-------------------------------|--|---|-----|----|----|
| $t_{d(on)}$ | Turn-On Delay Time | $V_{DD} = -15\text{ V}, I_D = -9.5\text{ A}, V_{GS} = -10\text{ V}, R_{GEN} = 6\ \Omega$ | – | 11 | 20 | ns |
| t_r | Rise Time | | – | 10 | 20 | |
| $t_{d(off)}$ | Turn-off Delay Time | | – | 44 | 71 | |
| t_f | Fall Time | | – | 26 | 42 | |
| Q_g | Total Gate Charge | $V_{GS} = 0\text{ V to } -10\text{ V}, V_{DD} = -15\text{ V}, I_D = -9.5\text{ A}$ | – | 46 | 65 | nC |
| Q_g | Total Gate Charge | $V_{GS} = 0\text{ V to } -5\text{ V}, V_{DD} = -15\text{ V}, I_D = -9.5\text{ A}$ | – | 26 | 37 | nC |
| Q_{gs} | Gate to Source Charge | $V_{DD} = -15\text{ V}, I_D = -9.5\text{ A}$ | – | 6.4 | – | nC |
| Q_{gd} | Gate to Drain "Miller" Charge | $V_{DD} = -15\text{ V}, I_D = -9.5\text{ A}$ | – | 13 | – | nC |

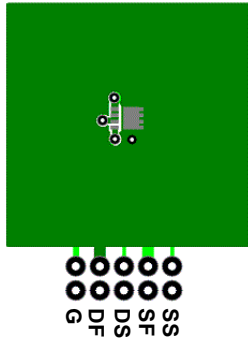
DRAIN-SOURCE DIODE CHARACTERISTICS

| | | | | | | |
|----------|---------------------------------------|---|---|-------|------|----|
| V_{SD} | Source to Drain Diode Forward Voltage | $V_{GS} = 0\text{ V}, I_S = -9.5\text{ A (Note 2)}$ | – | –0.89 | –1.3 | V |
| | | $V_{GS} = 0\text{ V}, I_S = -1.6\text{ A (Note 2)}$ | – | –0.73 | –1.2 | V |
| t_{rr} | Reverse Recovery Time | $I_F = -9.5\text{ A}, di/dt = 100\text{ A}/\mu\text{s}$ | – | 24 | 38 | ns |
| Q_{rr} | Reverse Recovery Charge | | – | 15 | 27 | nC |

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

NOTES:

- $R_{\theta JA}$ is determined with the device mounted on a 1 in² pad 2 oz copper pad on a 1.5 × 1.5 in. board of FR-4 material. $R_{\theta CA}$ is determined by the user's board design.



a) 53°C/W when mounted on a 1 in² pad of 2 oz copper



b) 125°C/W when mounted on a minimum pad

- Pulse Test: Pulse Width < 300 μs , Duty cycle < 2.0%.
- The diode connected between the gate and source serves only as protection against ESD. No gate overvoltage rating is implied.

TYPICAL CHARACTERISTICS

($T_J = 25^\circ\text{C}$ unless otherwise noted)

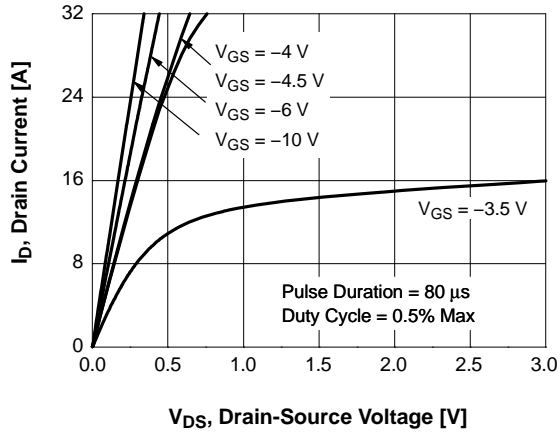


Figure 1. On-Region Characteristics

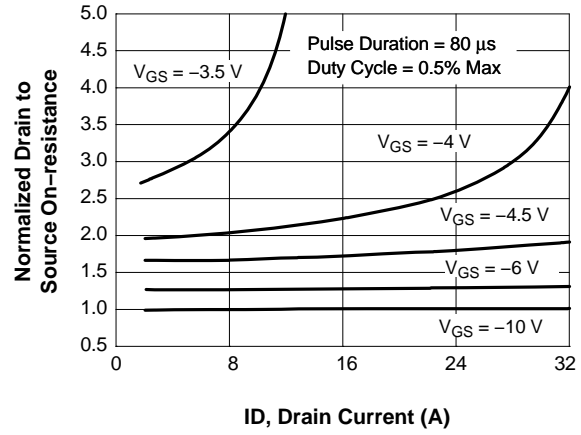


Figure 2. Normalized On-Resistance vs Drain Current and Gate Voltage

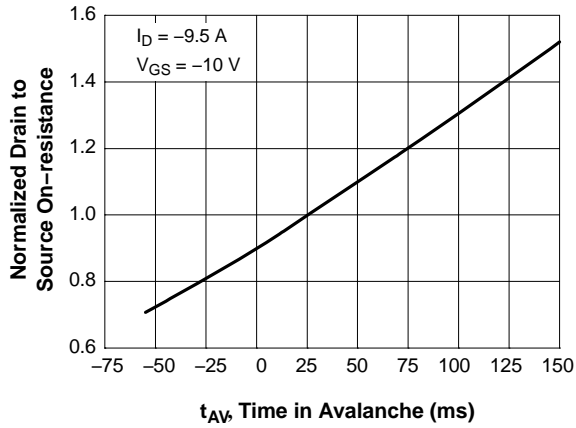


Figure 3. Normalized On Resistance vs Junction Temperature

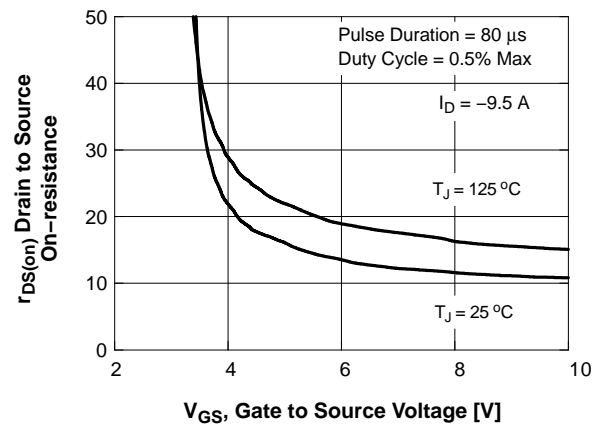


Figure 4. On-Resistance vs Gate to Source Voltage

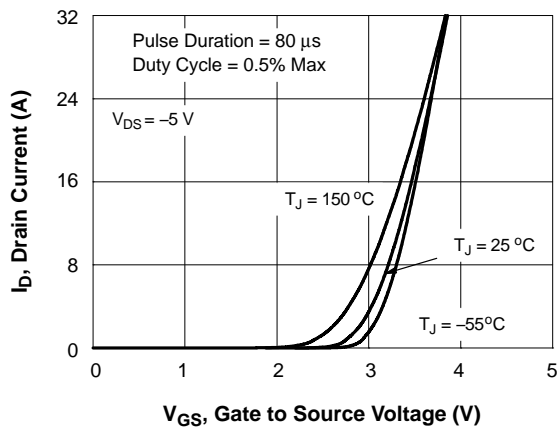


Figure 5. Transfer Characteristics

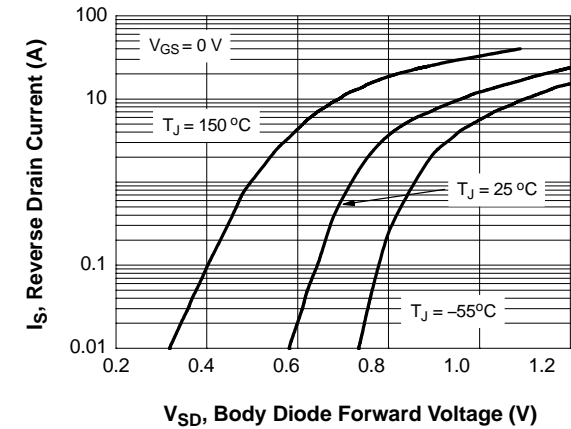


Figure 6. Source to Drain Diode Forward Voltage vs Source Current

TYPICAL PERFORMANCE CHARACTERISTICS (Continued)

($T_J = 25^\circ\text{C}$ unless otherwise noted)

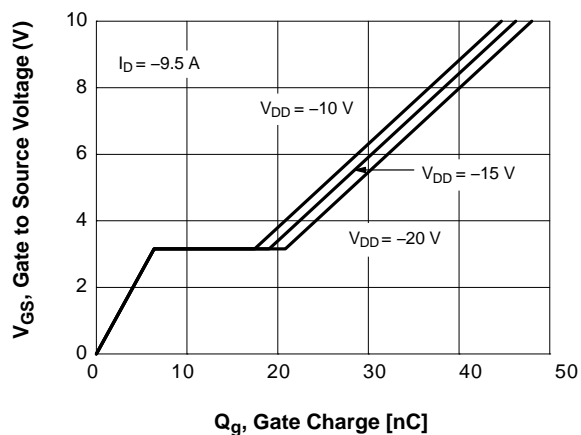


Figure 7. Gate Charge Characteristics

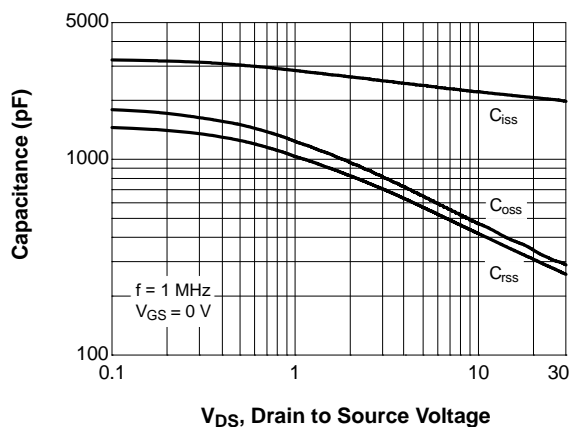


Figure 8. Capacitance vs Drain to Source Voltage

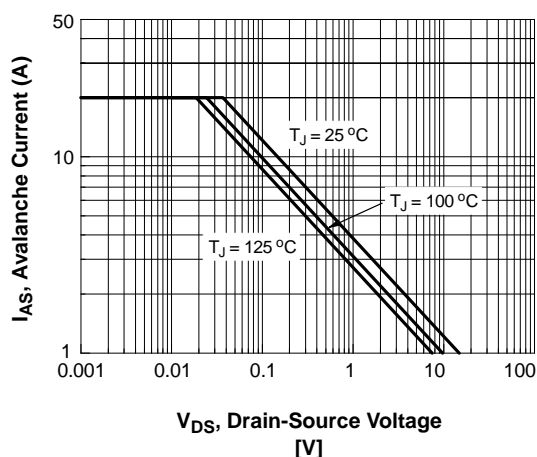


Figure 9. Unclamped Inductive Switching Capability

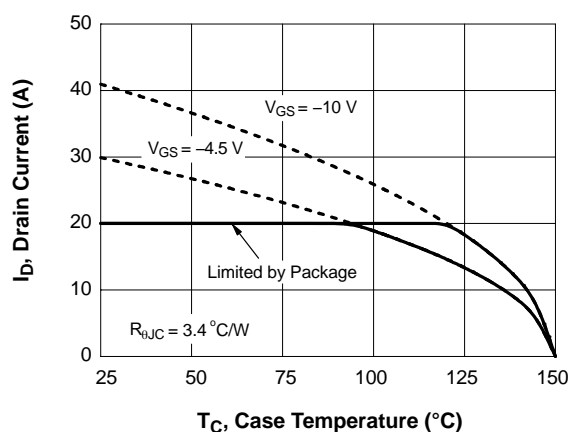


Figure 10. Maximum Continuous Drain Current vs Case Temperature

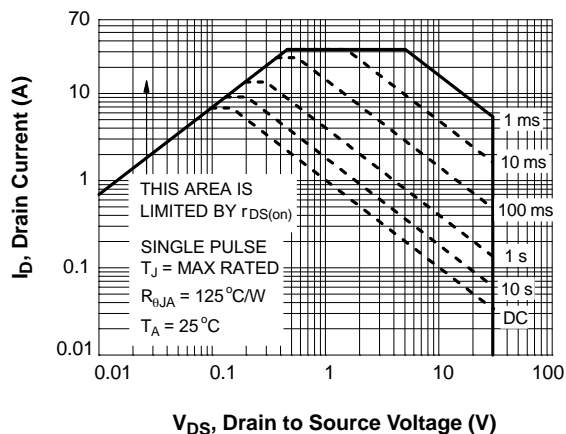


Figure 11. Forward Bias Safe Operating Area

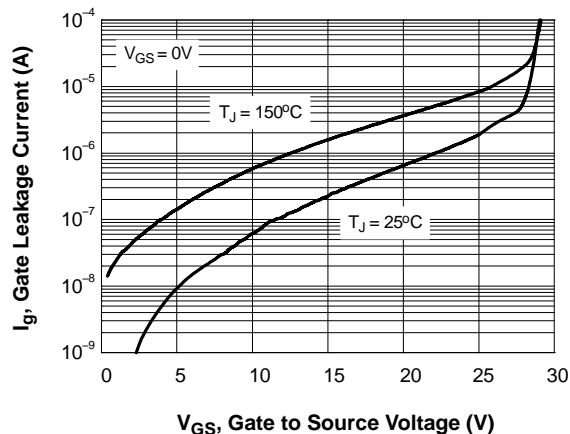


Figure 12. I_{gss} vs V_{gss}

TYPICAL PERFORMANCE CHARACTERISTICS (Continued)

($T_J = 25^\circ\text{C}$ unless otherwise noted)

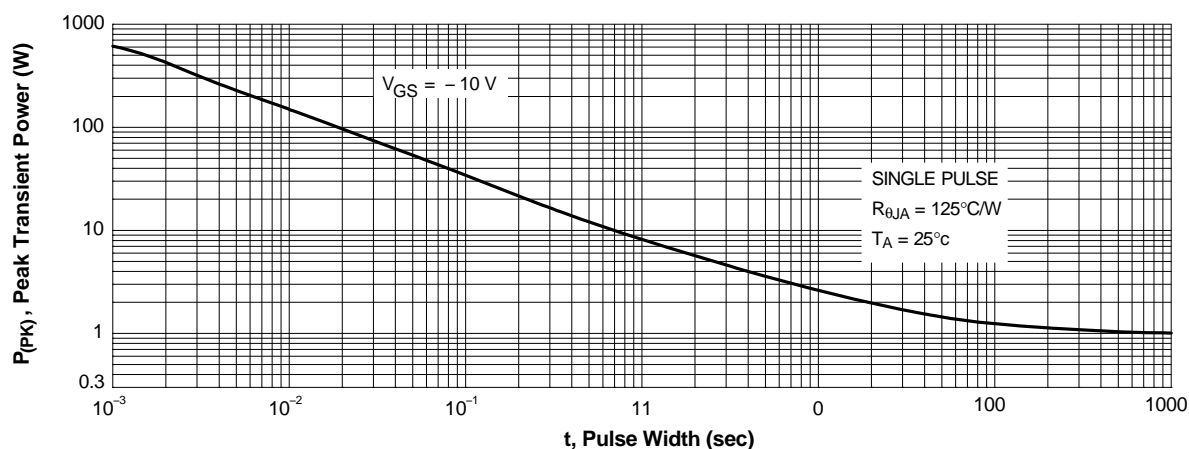


Figure 13. Single Pulse Maximum Power Dissipation

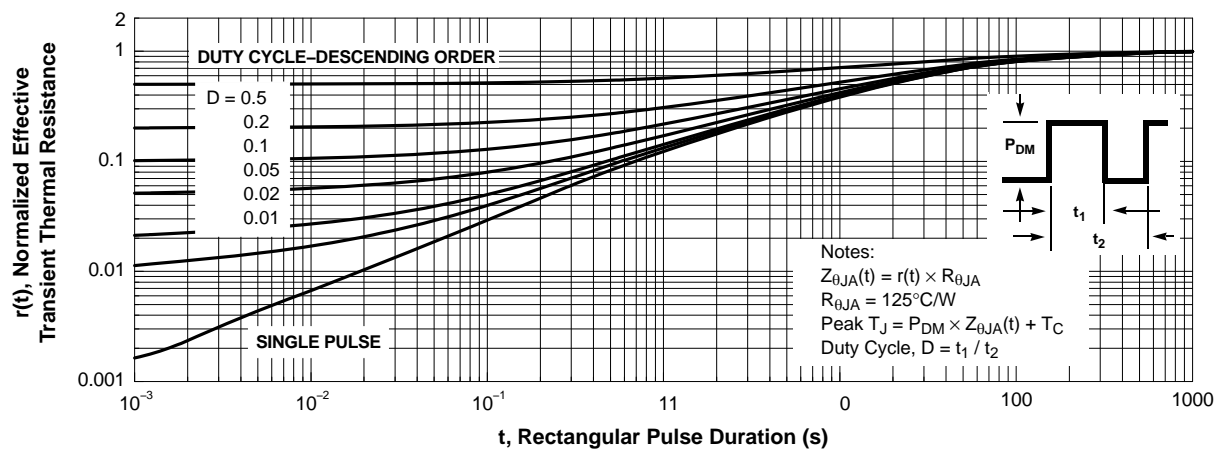


Figure 14. Junction-to-Ambient Transient Thermal Response Curve

onsemi, **Onsemi**, and other names, marks, and brands are registered and/or common law trademarks of Semiconductor Components Industries, LLC dba "**onsemi**" or its affiliates and/or subsidiaries in the United States and/or other countries. **onsemi** owns the rights to a number of patents, trademarks, copyrights, trade secrets, and other intellectual property. A listing of **onsemi**'s product/patent coverage may be accessed at www.onsemi.com/site/pdf/Patent-Marking.pdf. **onsemi** reserves the right to make changes at any time to any products or information herein, without notice. The information herein is provided "as-is" and **onsemi** makes no warranty, representation or guarantee regarding the accuracy of the information, product features, availability, functionality, or suitability of its products for any particular purpose, nor does **onsemi** assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. Buyer is responsible for its products and applications using **onsemi** products, including compliance with all laws, regulations and safety requirements or standards, regardless of any support or applications information provided by **onsemi**. "Typical" parameters which may be provided in **onsemi** data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. **onsemi** does not convey any license under any of its intellectual property rights nor the rights of others. **onsemi** products are not designed, intended, or authorized for use as a critical component in life support systems or any FDA Class 3 medical devices or medical devices with a same or similar classification in a foreign jurisdiction or any devices intended for implantation in the human body. Should Buyer purchase or use **onsemi** products for any such unintended or unauthorized application, Buyer shall indemnify and hold **onsemi** and its officers, employees, subsidiaries, affiliates, and distributors harmless against all claims, costs, damages, and expenses, and reasonable attorney fees arising out of, directly or indirectly, any claim of personal injury or death associated with such unintended or unauthorized use, even if such claim alleges that **onsemi** was negligent regarding the design or manufacture of the part. **onsemi** is an Equal Opportunity/Affirmative Action Employer. This literature is subject to all applicable copyright laws and is not for resale in any manner.

PUBLICATION ORDERING INFORMATION

LITERATURE FULFILLMENT:

Email Requests to: orderlit@onsemi.com

onsemi Website: www.onsemi.com

TECHNICAL SUPPORT

North American Technical Support:

Voice Mail: 1 800-282-9855 Toll Free USA/Canada

Phone: 011 421 33 790 2910

Europe, Middle East and Africa Technical Support:

Phone: 00421 33 790 2910

For additional information, please contact your local Sales Representative